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Crystalline gallium nitride and method for forming crystalline gallium nitride**Publication number:** JP2003511326T**Publication date:** 2003-03-25**Inventor:****Applicant:****Classification:**

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A gallium nitride growth process forms crystalline gallium nitride. The process comprises the steps of providing a source gallium nitride; providing mineralizer; providing solvent; providing a capsule; disposing the source gallium nitride, mineralizer and solvent in the capsule; sealing the capsule; disposing the capsule in a pressure cell; and subjecting the pressure cell to high pressure and high temperature (HPHT) conditions for a length of time sufficient to dissolve the source gallium nitride and precipitate the source gallium nitride into at least one gallium nitride crystal. The invention also provides for gallium nitride crystals formed by the processes of the invention.

